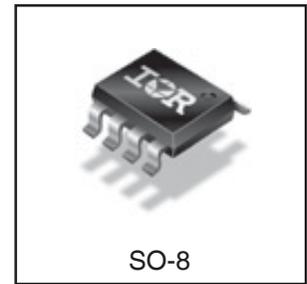
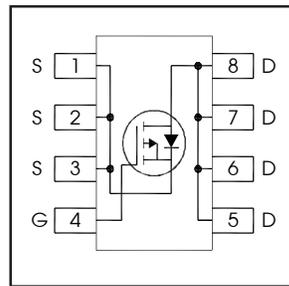


# IRF9393PbF

HEXFET® Power MOSFET

$V_{DS}$	<b>-30</b>	<b>V</b>
$V_{GS\ max}$	<b>±25</b>	<b>V</b>
$R_{DS(on)\ max}$ (@ $V_{GS} = -10V$ )	<b>19.4</b>	<b>mΩ</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>-9.2</b>	<b>A</b>



## Applications

- Adaptor Input Switch for Notebook PC

## Features and Benefits

### Features

25V $V_{GS\ max}$
Industry-Standard SO8 Package
RoHS Compliant Containing no Lead, no Bromide and no Halogen

### Resulting Benefits

Direct Drive at High $V_{GS}$
Multi-Vendor Compatibility
Environmentally Friendlier

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRF9393PbF	SO8	Tube/Bulk	95	
IRF9393TRPbF	SO8	Tape and Reel	4000	

## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	-30	V
$V_{GS}$	Gate-to-Source Voltage	± 25	
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-9.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-7.3	
$I_{DM}$	Pulsed Drain Current ①	-75	
$P_D @ T_A = 25^\circ C$	Power Dissipation ④	2.5	W
$P_D @ T_A = 70^\circ C$	Power Dissipation ④	1.6	
	Linear Derating Factor	0.02	W/°C
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C

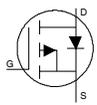
## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
B <sub>V</sub> DSS	Drain-to-Source Breakdown Voltage	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔB <sub>V</sub> DSS/ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.019	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	13.3	—	mΩ	V <sub>GS</sub> = -20V, I <sub>D</sub> = -9.2A ③
		—	15.6	19.4		V <sub>GS</sub> = -10V, I <sub>D</sub> = -9.2A ③
		—	25.6	32.5		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -7.5A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	-1.3	-1.8	-2.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -25μA
ΔV <sub>GS(th)</sub>	Gate Threshold Voltage Coefficient	—	-5.7	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-1.0	μA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
		—	—	-150		V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-10	μA	V <sub>GS</sub> = -25V
	Gate-to-Source Reverse Leakage	—	—	10		V <sub>GS</sub> = 25V
g <sub>fs</sub>	Forward Transconductance	13	—	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -7.5A
Q <sub>g</sub>	Total Gate Charge ⑥	—	14	—	nC	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -7.5A
Q <sub>g</sub>	Total Gate Charge ⑥	—	25	38	nC	V <sub>GS</sub> = -10V
Q <sub>gs</sub>	Gate-to-Source Charge ⑥	—	3.5	—		V <sub>DS</sub> = -15V
Q <sub>gd</sub>	Gate-to-Drain Charge ⑥	—	6.4	—		I <sub>D</sub> = -7.5A
R <sub>G</sub>	Gate Resistance ⑥	—	15	—	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	16	—	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -4.5V ③
t <sub>r</sub>	Rise Time	—	44	—		I <sub>D</sub> = -1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	55	—		R <sub>G</sub> = 6.8Ω
t <sub>f</sub>	Fall Time	—	49	—		See Figs. 20a & 20b
C <sub>iss</sub>	Input Capacitance	—	1110	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	230	—		V <sub>DS</sub> = -25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	160	—		f = 1.0MHz

## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	100	mJ
I <sub>AR</sub>	Avalanche Current ①	—	-7.5	A

## Diode Characteristics

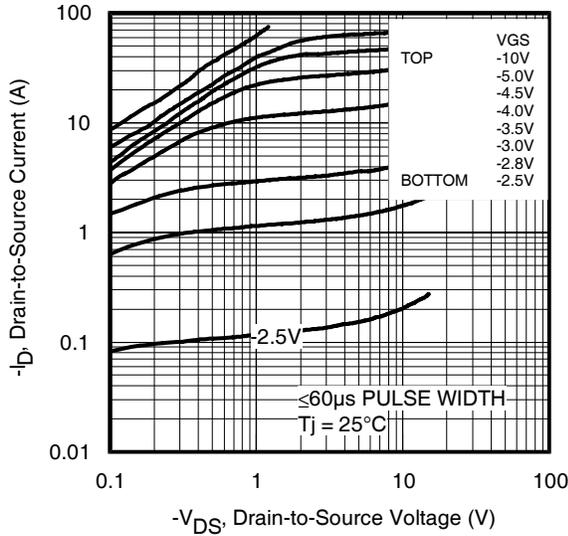
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-75		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -2.5A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	24	36	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -2.5A, V <sub>DD</sub> = -24V
Q <sub>rr</sub>	Reverse Recovery Charge	—	15	23	nC	di/dt = 100A/μs ③

## Thermal Resistance

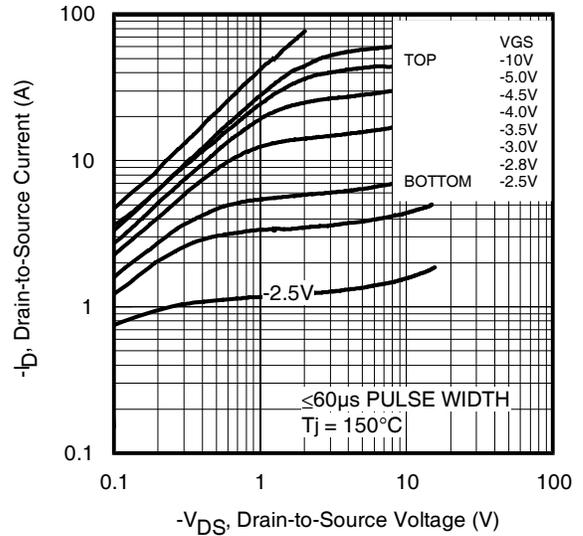
	Parameter	Typ.	Max.	Units
R <sub>θJL</sub>	Junction-to-Drain Lead ⑤	—	20	°C/W
R <sub>θJA</sub>	Junction-to-Ambient ④	—	50	

### Notes:

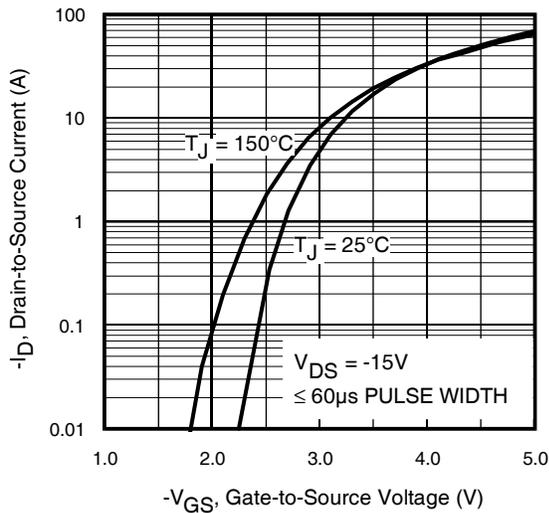
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting T<sub>J</sub> = 25°C, L = 3.5mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = -7.5A.
- ③ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ④ When mounted on 1 inch square copper board.
- ⑤ R<sub>θ</sub> is measured at T<sub>J</sub> of approximately 90°C.
- ⑥ For DESIGN AID ONLY, not subject to production testing.



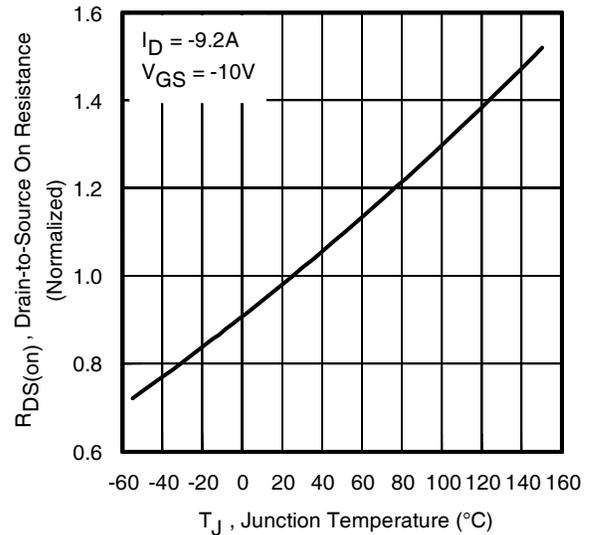
**Fig 1.** Typical Output Characteristics



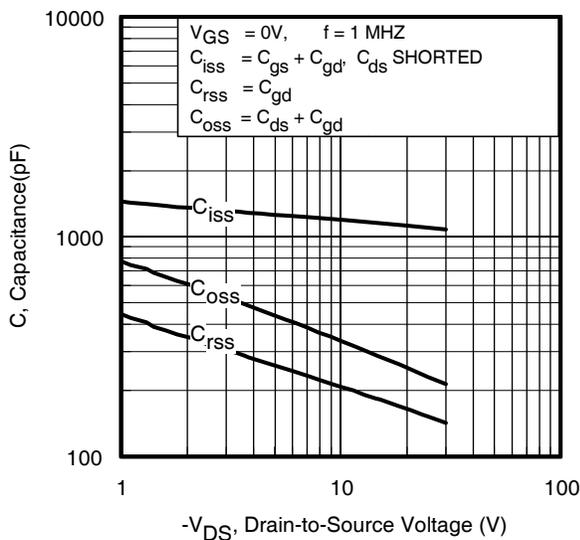
**Fig 2.** Typical Output Characteristics



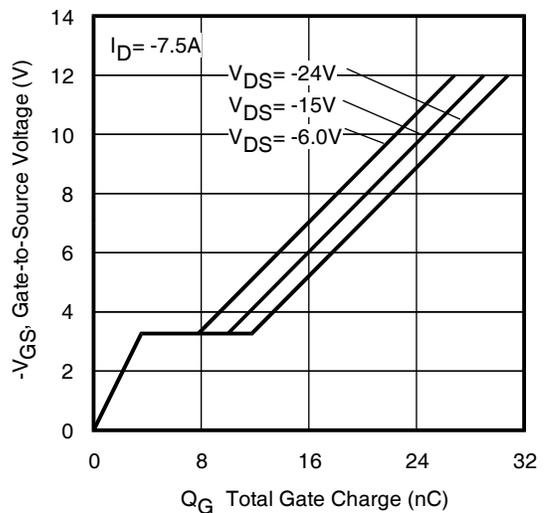
**Fig 3.** Typical Transfer Characteristics



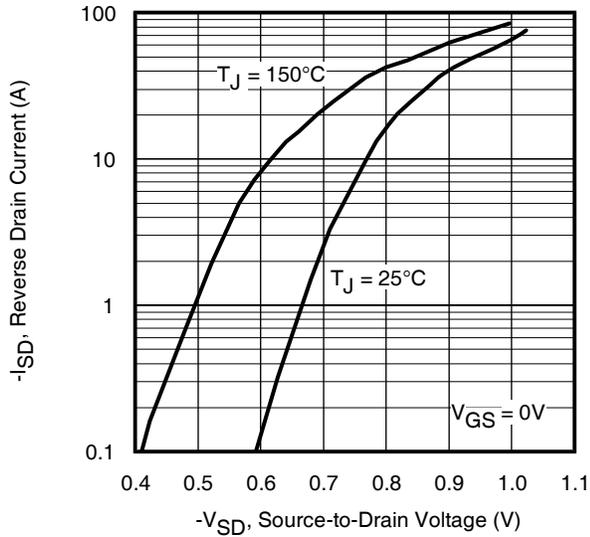
**Fig 4.** Normalized On-Resistance vs. Temperature



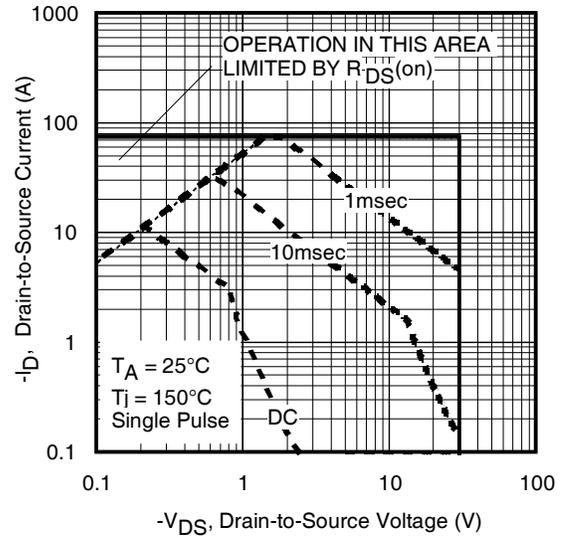
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage  
[www.irf.com](http://www.irf.com)



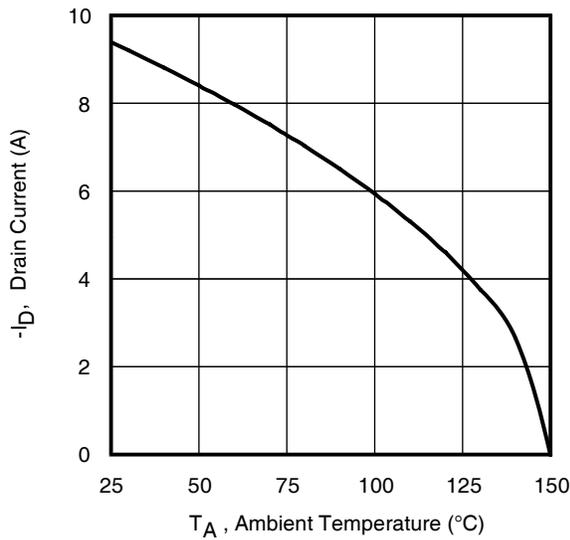
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



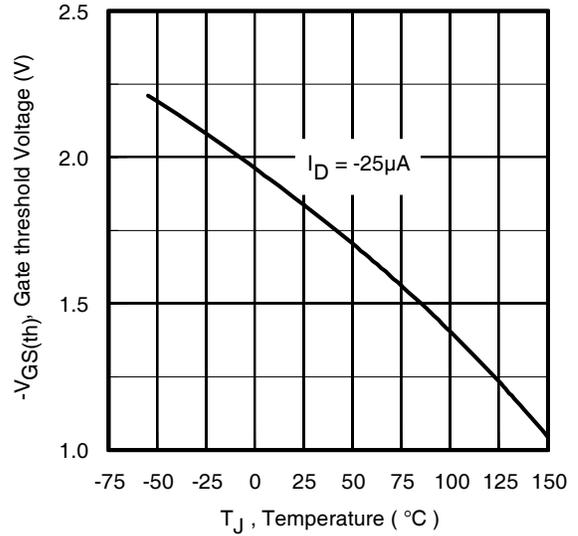
**Fig 7.** Typical Source-Drain Diode Forward Voltage



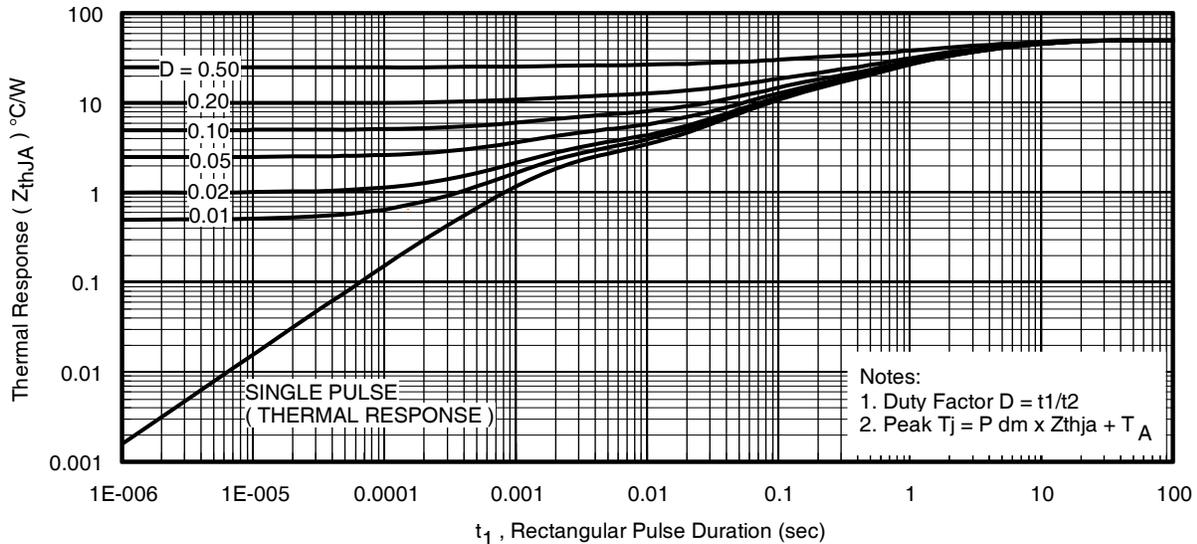
**Fig 8.** Maximum Safe Operating Area



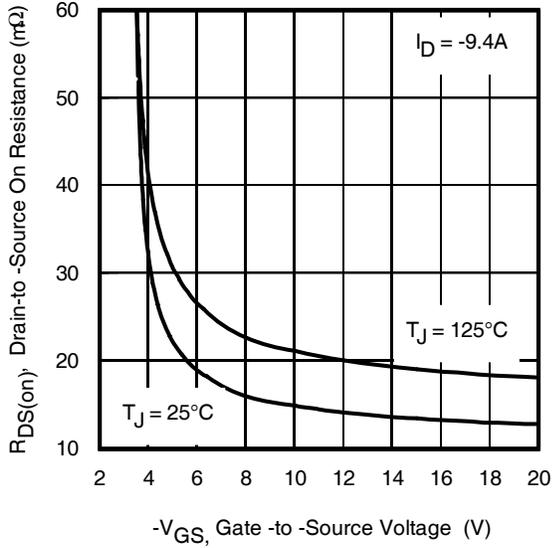
**Fig 9.** Maximum Drain Current vs. Ambient Temperature



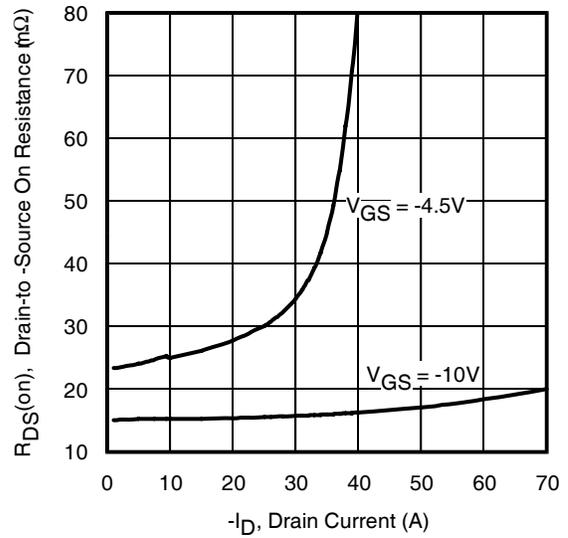
**Fig 10.** Threshold Voltage vs. Temperature



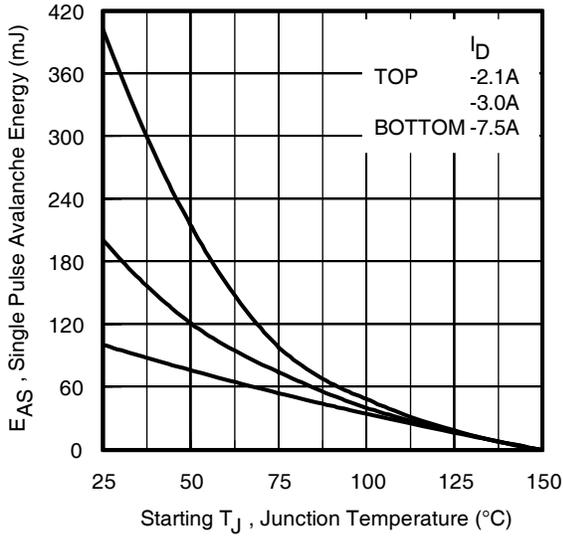
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



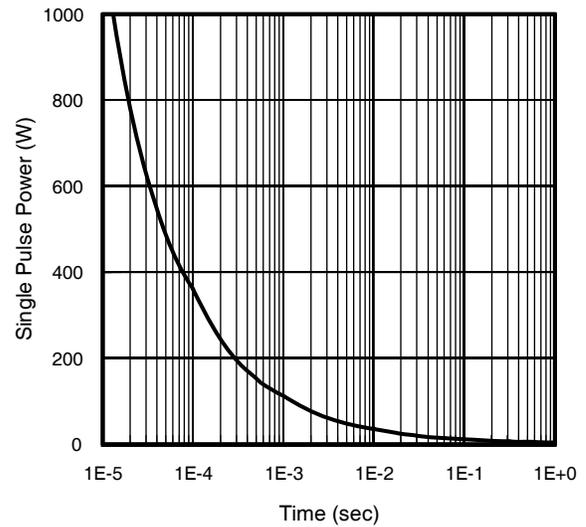
**Fig 12.** On-Resistance vs. Gate Voltage



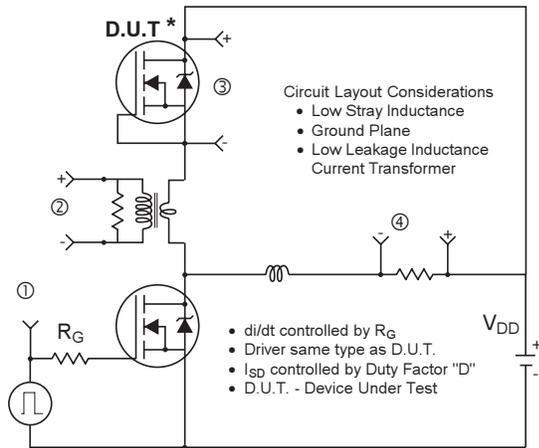
**Fig 13.** Typical On-Resistance vs. Drain Current



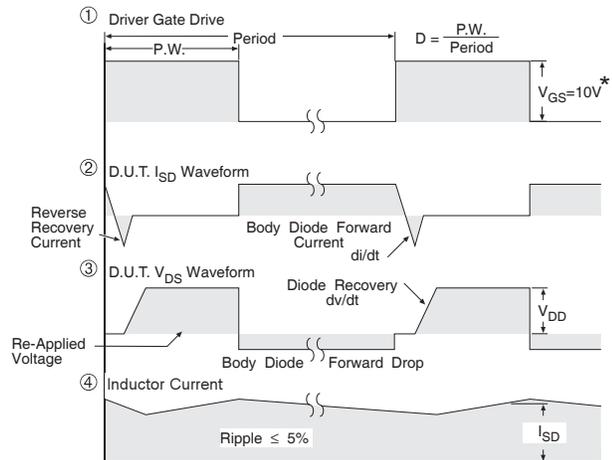
**Fig 14.** Maximum Avalanche Energy vs. Drain Current



**Fig 16.** Typical Power vs. Time

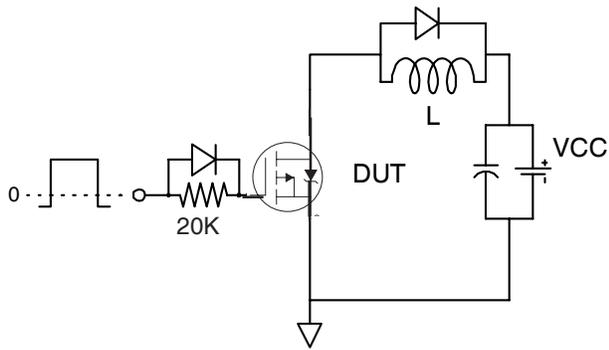


\* Reverse Polarity of D.U.T. for P-Channel

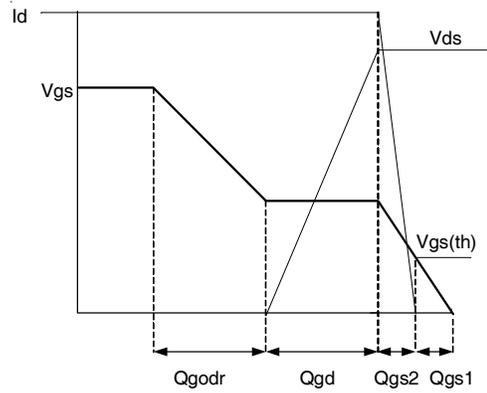


\*  $V_{GS} = 5V$  for Logic Level Devices

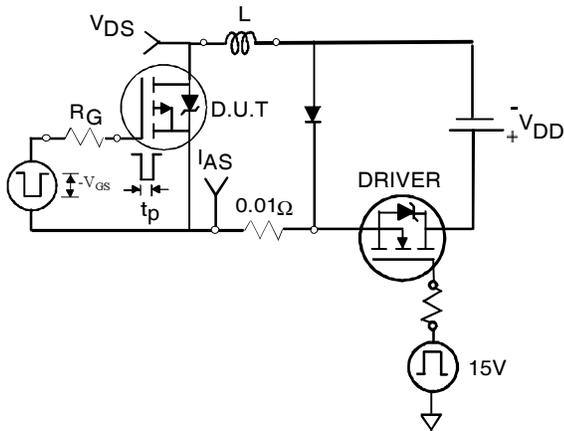
**Fig 17.** Diode Reverse Recovery Test Circuit for P-Channel HEXFET® Power MOSFETs



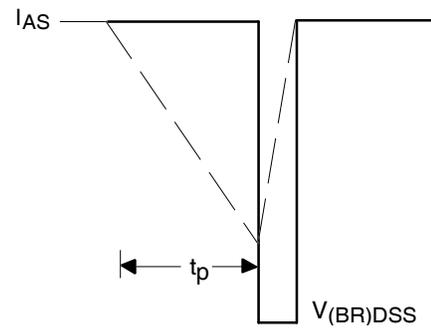
**Fig 18a.** Gate Charge Test Circuit



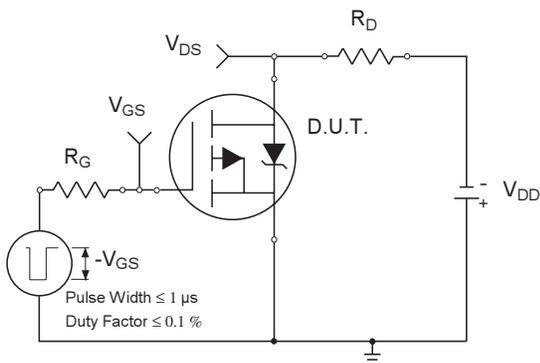
**Fig 18b.** Gate Charge Waveform



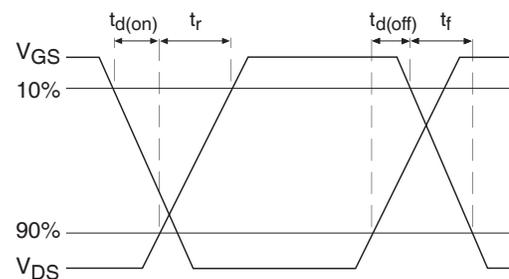
**Fig 19a.** Unclamped Inductive Test Circuit



**Fig 19b.** Unclamped Inductive Waveforms



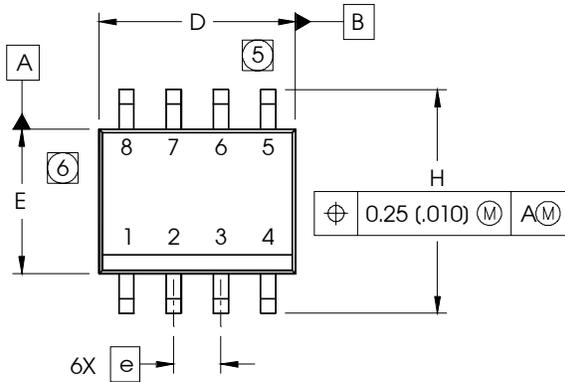
**Fig 20a.** Switching Time Test Circuit



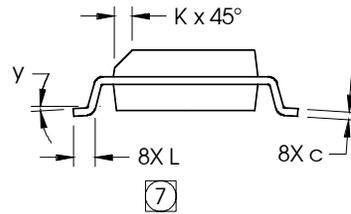
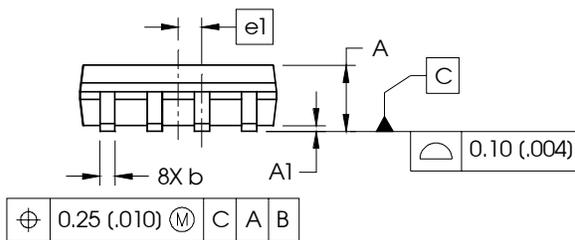
**Fig 20b.** Switching Time Waveforms

## SO-8 Package Outline (MOSFET & Fetky)

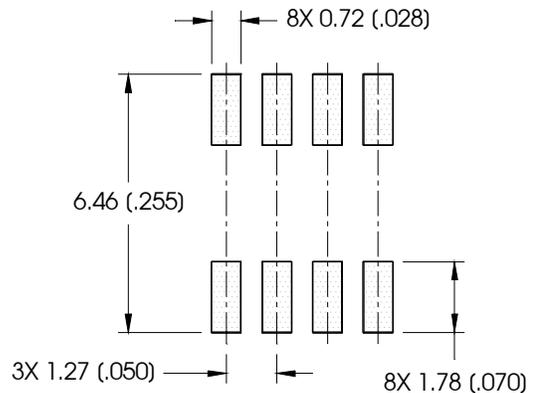
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



### FOOTPRINT

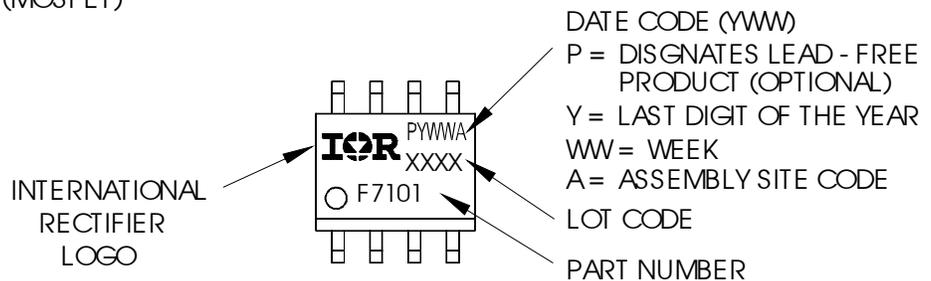


### NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

## SO-8 Part Marking Information

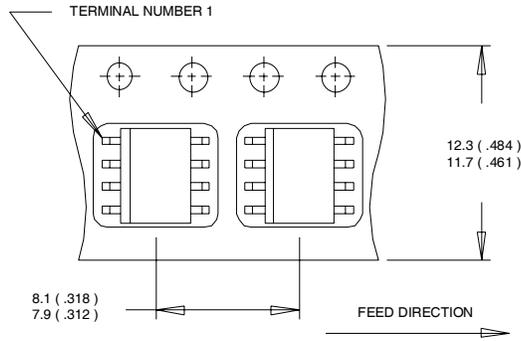
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



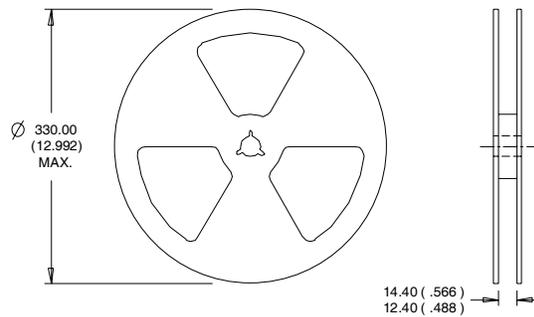
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

# IRF9393PbF

SO-8 Tape and Reel (Dimensions are shown in millimeters (inches))



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

## Qualification Information†

Qualification level	Consumer ††	
	(per JEDEC JESD47F††† guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D†††)
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site  
<http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements.  
Please contact your International Rectifier sales representative for further information:  
<http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

Data and specifications subject to change without notice.

# AMEYA360

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Email [amall@ameya360.com](mailto:amall@ameya360.com)

QQ 800077892

Skype [ameyasales1](#) [ameyasales2](#)

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